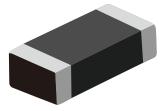


# **FEATURES**

Fast response, instantly clamping the transient over voltage.

- High surge current handling capability.
- High energy absorption capability.
- Low clamping voltages, providing better surge protection.
- Low capacitance values, providing digital switching circuitryprotection.
- High insulation resistance, preventing electric arcing to the adjacent

devices or circuits.



### **APPROVALS**

RoHS Compliance with 2011/65/EU HF Compliance with IEC61249-2-21:2003

# **APPLICATIONS**

Universal Serial Bus (USB).	
Mobile communication.	
Computer/DSP product.	
Video and audio ports.	

Portable/Hand-Held Products.

Data, Diagnostic I/O ports.

## **ELECTRICAL SPECIFICATION**

Test condition		
Varistor voltage	In = 1 mA DC	
Leakage current	Vdc = 5.5 V DC	
Maximum clamping voltage	Ic = 1 A	
Rated peak single pulse transient current	8 / 20 μs waveform, +/- each 1 time induce	
Capacitance	10/1000 μs waveform	
Insulation resistance after reflow soldering	f = 1MHz, Vrms = 0.5 V	



## **ELECTRICAL SPECIFICATION**

Electrical specification			
Maximum allowable continuous DC voltage	5.5	V	
trigger voltage / Varistor voltage / breakdown voltage	15-25	V	
Maximum clamping voltage	45	V	Maximum
Rated peak single pulse transient current	1	А	Maximum
Nonlinearity coefficient	> 12		
Leakage current at continuous DC voltage	< 0.1	μΑ	
Response time	< 0.5	ns	
Varistor voltage temperature coefficient	< 0.05	%/°C	
Capacitance measured at 1MHz	50	pF	Typical
Capacitance tolerance	-50 to +50	%	
Insulation resistance after reflow soldering on PCB	> 10	MΩ	
Operating ambient temperature	-55 to +125	°C	
Storage temperature	-55 to +125	°C	



## **RELIABILITY TESTING PROCEDURES**

Reliability parameter		Test methods and remarks	Test requirement
Pulse current capability	lmax 8/20 μs	IEC 1051-1, Test 4.5. 10 pulses in the same direction at 2 pulses per minute at maximum peak current	d Vn /Vn≤10% no visible damage
Electrostatic discharge capability	ESD C=150 pF, R=330Ω	IEC 1000-4-2 Each 10 times in positive/negative direction in 10 sec at 15KV air discharge, 8KV contact discharge (Level 4)	d Vn /Vn≤10% no visible damage
	Thermal shock	IEC 68-2-14 Condition for 1 cycle Step 1 : Min. –40°C, 30±3 min. Step 2 : Max. +125°C, 30±3 min. Number of cycles: 30 times	d Vn /Vn≤5% no visible damage
	Low temperature	IEC 68-2-1 Place the chip at -40 $\pm$ 5°C for 1000 $\pm$ 12hrs. Remove and place for 24 $\pm$ 2hrs at room temp. condition, then measure	d Vn /Vn≤5% no visible damage
Environmenta	High temperature	IEC 68-2-2 Place the chip at $125\pm5^{\circ}$ C for $1000\pm24$ hrs. Remove and place for $24\pm2$ hrs at room temp. condition, then measure	d Vn /Vn≤5% no visible damage
l reliability	Heat resistance	IEC 68-2-3 Apply the rated voltage for 1000±48hrs at 85±3°C. Remove and place for 24±2hrs at room temp. condition, then measure	d Vn /Vn≤5% no visible damage
	Humidity resistance	IEC 68-2-30 Place the chip at 40±2°C and 90 to 95% humidity for 1000±24hrs. Remove and place for 24±2hrs at room temp. condition, then measure	d Vn /Vn≤5% no visible damage
	Pressure cooker test	Place the chip at 2 atm, 120°C, 85%RH for 60 hrs. Remove and place for $24\pm 2$ hrs at room temp. condition, then measure	d Vn /Vn≤10% no visible damage
	Operating life	Apply the rated voltage for $1000\pm48$ hrs at $125\pm3^{\circ}$ C. Remove and place for $24\pm2$ hrs at room temp. condition, then measure	d Vn /Vn≤10% no visible damage
Mechanical Reliability	Adhesive strength	IEC 68-2-22 Applied force on SMD chip by fracture from PCB	Strength>10 N no visible damage



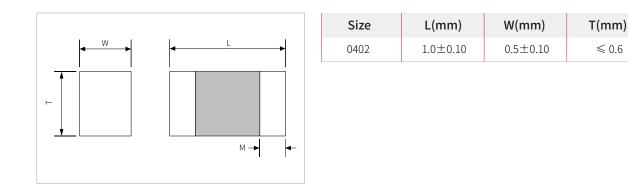
M(mm)

 $0.20 \pm 0.10$ 

## MATERIAL SPECIFICATION

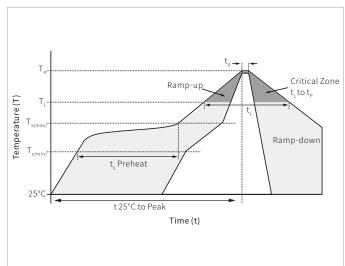
Body	Internal electrode	External electrode	Thickness of Ni/Sn plating layer	
ZnO based ceramics	Silver – Palladium	Silver – Nickel – Tin	Nickel $> 1\mu\text{m},$ Tin $> 2\mu\text{m}$	

## **DIMENSION SPECIFICATION**



## **SOLDERING RECOMMENDATIONS**

Reflow Condition		Lead-free assembly
Temperature Max (T <sub>s(min)</sub> )		150°C
Pre Heat	Temperature Max (T <sub>s(max)</sub> )	200°C
	Time (min to max) (t <sub>s</sub> )	60 – 180 secs
Average rar	np up rate (Liquidus Temp (T $_{\scriptscriptstyle L}$ ) to peak	3°C/second max
$T_{s(max)}$ to $T_{L}$ - Ramp-up Rate		3°C/second max
Reflow	Temperature (T <sub>L</sub> ) (Liquidus)	217°C
Rellow	Time (min to max) $(t_{L})$	60 – 150 seconds
Peak Temperature (T,)		260°C
Time within 5°C of actual peak Temperature ( $t_p$ )		20 – 40 seconds
Ramp-down Rate		6°C/second max
Time 25°C to peak Temperature (T,)		8 minutes max.
Do not exceed		260°C





### **DRDERING INF ORMATIOON**

Part Number	Package&Size	QTY/Reel	Reel Size
SME0402B5.5A	0402 (1.0 x 0.5 mm)	10000PCS	7"



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